



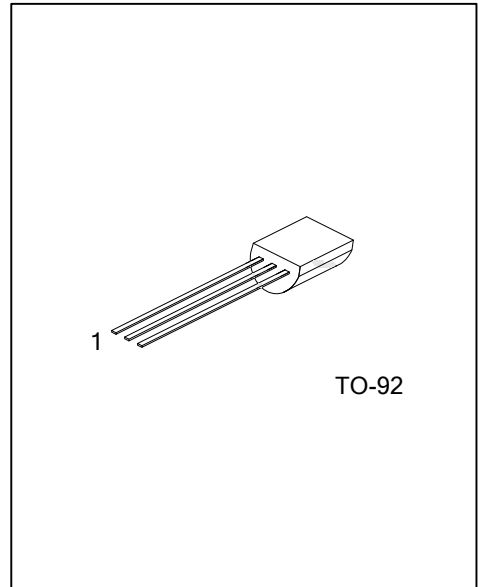
BC327/328

PNP EPITAXIAL SILICON TRANSISTOR

SWITCHING AND AMPLIFIER APPLICATIONS

FEATURES

- * Suitable for AF-Driver stages and low power output stages
- * Complement to UTC **BC337/338**



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BC327L-xx-T92-B	BC327G-xx-T92-B	TO-92	C	B	E	Tape Box
BC327L-xx-T92-K	BC327G-xx-T92-K	TO-92	C	B	E	Bulk
BC328L-xx-T92-B	BC328G-xx-T92-B	TO-92	C	B	E	Tape Box
BC328L-xx-T92-K	BC328G-xx-T92-K	TO-92	C	B	E	Bulk

Note: Pin Assignment: C: Collector B: Base E: Emitter

<p>BC327G-xx-T92-B</p> <p>(1) Packing Type (2) Package Type (3) Rank (4) Green Package</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) xx: refer to CLASSIFICATION OF h_{FE} (4) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING

BC327	BC328

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-emitter voltage	BC327	-50	V
	BC328	-30	V
Collector-emitter voltage	BC327	-45	V
	BC328	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current (DC)	I _C	-800	mA
Peak Base Current	I _{BM}	-200	mA
Collector dissipation	P _C	625	mW
Junction Temperature	T _J	+125	°C
Operating Temperature	T _{OPR}	-20 ~ +85	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	BC327	I _C =-10mA, I _B =0	-45			V
	BC328		-25			V
Collector-emitter breakdown voltage	BC327	I _C =-0.1mA, V _{BE} =0	-50			V
	BC328		-30			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =-10mA, I _C =0	-5			V
Collector Cut-off Current	BC327	V _{CE} =-45V, I _B =0		-2	-100	nA
	BC328	V _{CE} =-25V, I _B =0		-2	-100	nA
DC current gain		h _{FE1}	V _{CE} =-1V, I _C =-100mA	100		630
		h _{FE2}	V _{CE} =-1V, I _C =-300mA	40		
Collector-emitter saturation voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.7	V
Base-emitter on voltage	V _{BE(ON)}	V _{CE} =-1V, I _C =-300mA			-1.2	V
Current gain bandwidth product	f _T	V _{CE} =-5V, I _C =-10mA, f=20MHz		100		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		12		pF

■ CLASSIFICATION OF h_{FE}

RANK	16	25	40
h _{FE1}	100-250	160-400	250-630
h _{FE2}	60~	100~	170~

■ TYPICAL CHARACTERISTICS

Figure 1. Static Characteristic

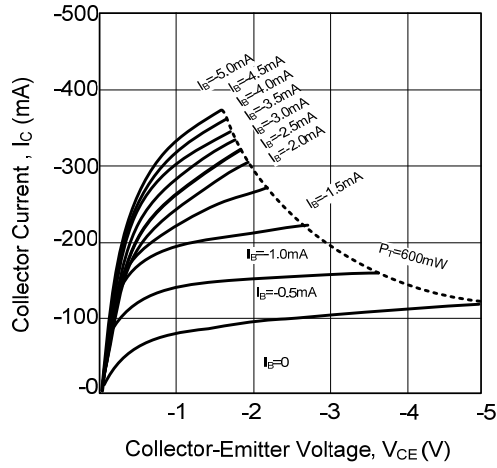


Figure 2. Static Characteristic

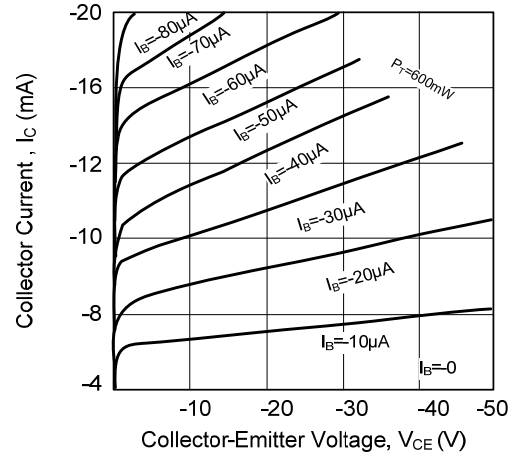


Figure 3. DC Current Gain

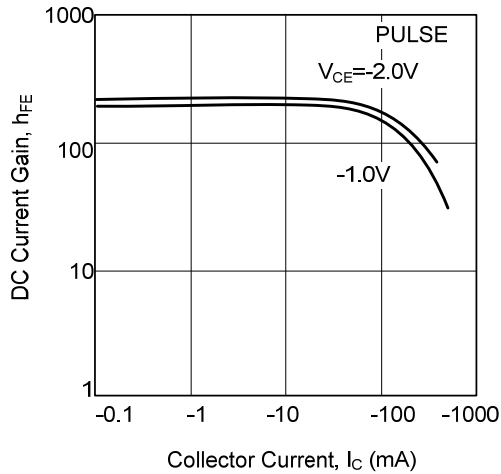


Figure 4. Base-Emitter Saturation Voltage vs. Collector-Emitter Saturation Voltage

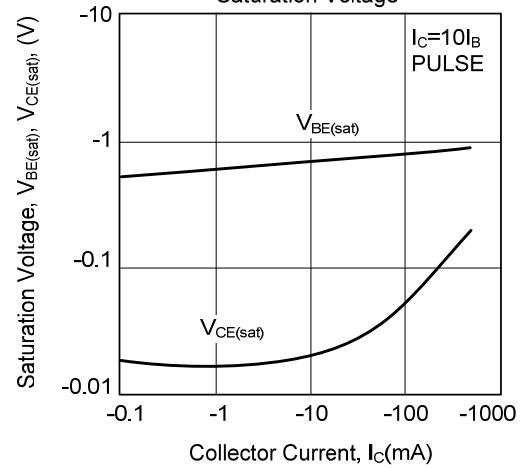


Figure 5. Base-Emitter On Voltage

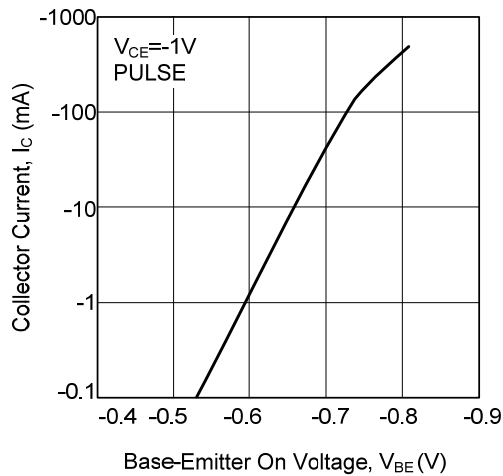
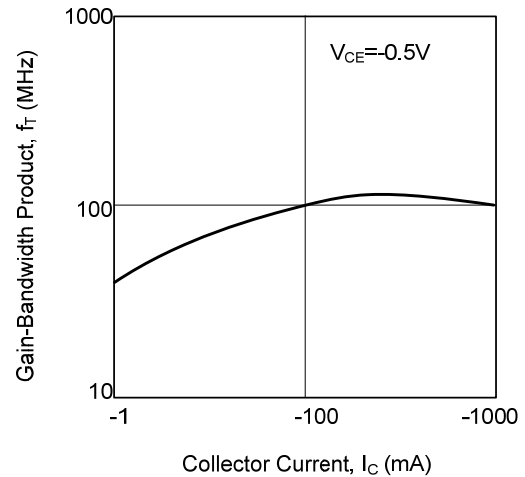


Figure 6. Gain Bandwidth Product



■ TYPICAL CHARACTERISTICS (Cont.)

Figure 5. Base-Emitter On Voltage

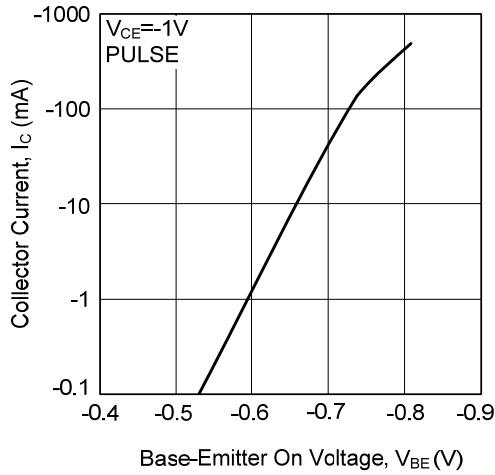


Figure 6. Gain Bandwidth Product

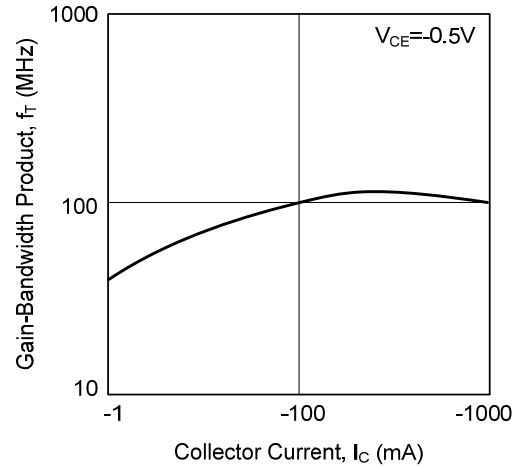
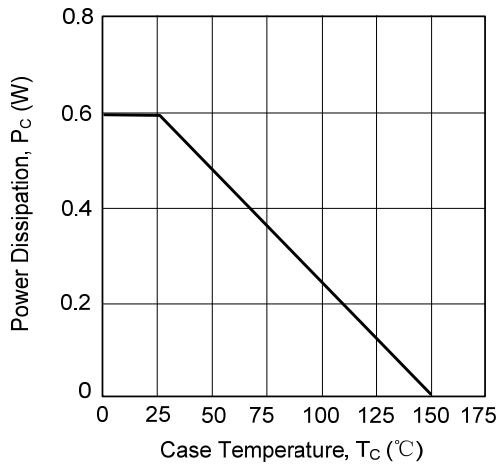


Figure 9. Power Derating



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